PNP/NPN Epitaxial Planar Silicon Transistors



2SB1295/2SD1935

Low-Frequency General-Purpose Amplifier Applications

Applications

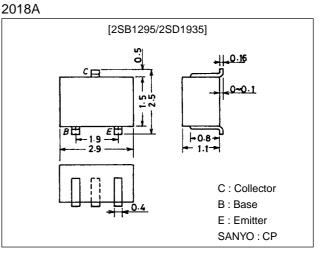
· AF power amplifier, medium-speed switching, smallsized motor drivers.

Features

- · Large current capacity.
- \cdot Low collector to emitter saturation voltage.
- Very small-sized package permitting sets to be made smaller and slimer.

Package Dimensions

unit:mm



():2SB1295

Specifications

Absolute Maximum Ratings at Ta = 25°C

-				
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		()15	V
Collector-to-Emitter Voltage	VCEO		()15	V
Emitter-to-Base Voltage	V _{EBO}		(–)5	V
Collector Current	ι _C		(-)0.8	A
Collector Current (Pulse)	I _{CP}		(-)3	A
Collector Dissipation	PC		200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

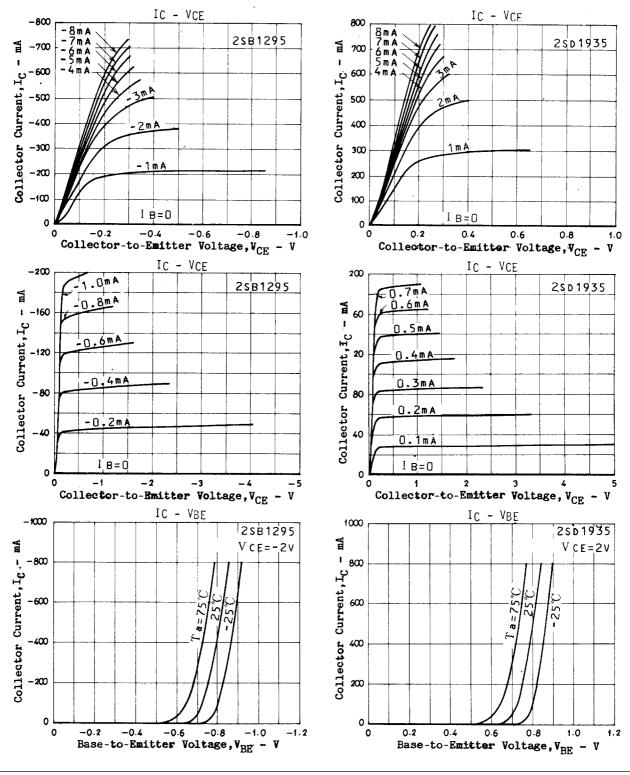
Parameter	Symbol	Conditions	Ratings			Unit
Falantelei		Conditions	min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =(-)12V, I _E =0			(–)100	nA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)100	nA
	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)50mA	135*		900*	
DC Current Gain					(600)	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)800mA	80			
* : The 2SB1295/2SD1935 are classified by 50	ows : Marking: 2SB1295 : UL	/2SD193	5 : CT			
2SB1295 135 5 270 200 6 400	300 7	600 h _{FE} rank: 2SB1295 : 5, 6	5, 7/2SD1	935 : 5,	6, 7, 8	
2SB1935 135 5 270 200 6 400	300 7	600 450 8 900				

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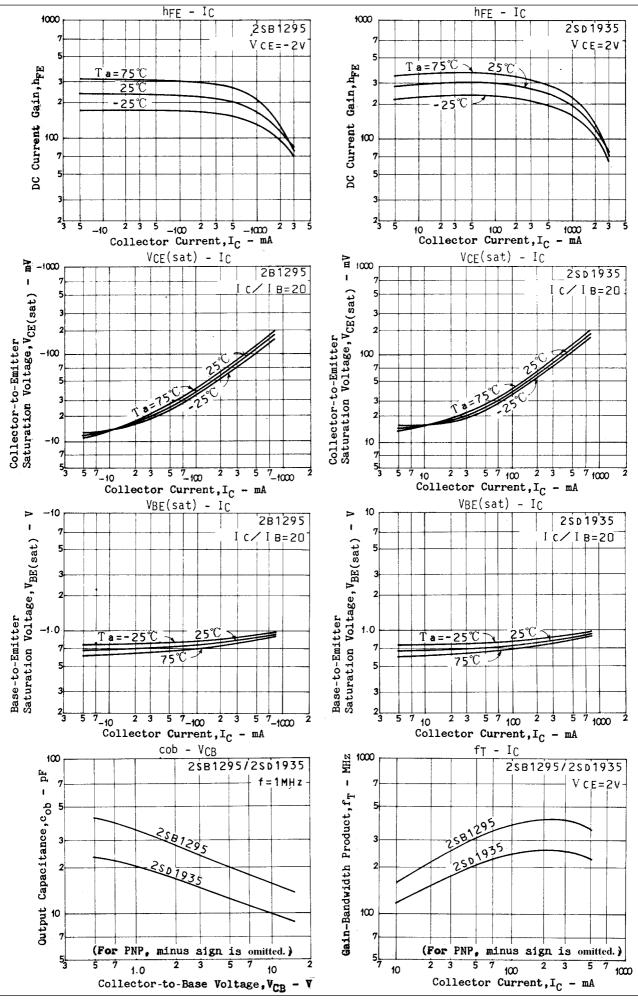
SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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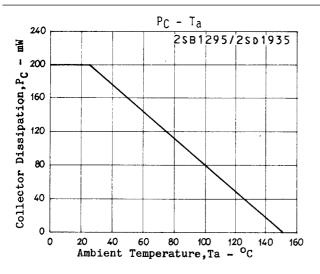
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Unit
Gain-Bandwidth Product	fT	V _{CE} =(-)2V, I _C =(-)50mA		200		MHz
				(300)		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(15)		pF
				10		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)} 1	I _C =(–)5mA, I _B =(–)0.5mA		(–)10	(–)25	mV
	V _{CE(sat)} ²	I _C =(-)400mA, I _B =(-)20mA		(–)100	(–)200	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)400mA, I _B =(-)20mA		(-)0.9	(–)1.2	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)10μA, I _E =0	(–)15			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(–)15			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)10μA, I _C =0	(–)5			V



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